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Atty. FORM PTO-1449 (modified) Dkt. No. To: U.S. Department of Commerce (PM&S FORM PAT-1449) Patent and Trademark Office F00-219-US-DIV-3 273686 Applicant; MANABE et al. INFORMATION DISCLOSURE STATEMENT BY APPLICANT Div. of Appln. No.: 09/417,778 Filing Date: October 14, 1999 Examiner: Minh Loan Tran Group Art Unit: 2811 1 Date: OCTOBER 2, 2000 Page and kutabelle rorabelt thruthing and ap-ana puntabelle robelt Matail Kutabelle seeme ana managana a kutabelle kalaksi seeme The state of the s իրդինիսի միստոր Հայրքում դանուրդ US PATENT DOCUMENTS Filing Date Class Sub Name Date Document Examiner's (if appropriate) Class (Family Name of First Inventor) MM/YYYY Number Initials* Manabe et al. 1/1994 5,278,433 AR Murdock 07/89 4.844,989 BR 10/83 Kobayashi 4,408,217 CR Jacob et al. 05/81 DR 4,268,842 04/91 Izumiya et al. 5,005,057 ER Khan et al. 09/86 FR 4,614,961 Charmakedze et al. 05/79 4,153,905 GR Akasaki et al. 08/89 HR 4,855,249 Manabe et al. 03/90 4,911,102 IR Kotaki et al. 08/90 4,945,548 JR 08/83 Ohki et al. 4,396,929 KR Natsuoka et al. 04/91 LR |5.006,908 Bagratishvili et al. 08/86 MR 4,608,581 Kobayashi et al. 10/84 NR 4,473,938 er en de de la companya de la compa La companya de la companya del companya de la companya del companya de la companya del companya del companya del companya del companya de la companya del c Translation FOREIGN: PATENT DOCUMENTS Readily Abstract SubClass Available Inventor Name Class Country Document Date **MM/YYYY** Number Enclose No Enclosed No × Japan 09/1990 2-229475 OR x Japan 11/1990 PR 2-275682 x × Japan 04/1975 QR 5-042785 X Japan 12/1994 RR 59-228776 Nakahata 10/1994 Europe 0 620 203 A1 SR × EPA 08/1988 TR 0-277597 × Toyoda 02/1991 Japan 03-034549 UR x x Hatano Japan 02/1991 VR 34549 × Manabe Germany 09/1990 WR 4.006,449 KOBAYASHI Japan 01/1982 57-018377 XR OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.) English Abstract of OKI Japanese Application Published 9/22/82 under No. 57-153479. YR I. Akasaki et al., "Effects of AIN Buffer Layer on Crystallographic Structure... by MOVPE", ZR J. Crystal Growth 98 (1989) pp. 209-19. Liu et al., "Growth morphology and surface-acoustic-wave measurements of AIN films on Sapphire," Journal of Applied Physics, Vol. 46, No. 9, September 1975, pages 3703-3706. llegems et al. "Electrical properties of n-Type Vapor-growth Gallium Nitride", J. Phys. BBR Chem. sollds., 1973, V I. 34, pp. 885-895. Date Considered: Examiner Initial if citation considered, whither or not citation is in conformance with MPEP § 609. Draw line through citation if not *FXAMINER: in conformance and not considered. Include copy of this form with next communication to Applicant.

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